NSN 5962-01-305-5380

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Body Length:	
0.840 inches	
Body Width:	
0.310 inches	
Body Height:	
0.185 inches	
Maximum Power Dis	sipation Rating:
739.0 milliwatts	
Operating Tempurat	ure Range:
-55.0/+125.0 degrees	celsius
Storage Tempurature	e Range:
-65.0/+150.0 degrees	celsius
Features Provided:	
Monolithic and bipolar	and schottky and programmable and w/active pull-up
Inclosure Material:	
Ceramic	
Inclosure Configurat	ion:
Dual-in-line	
Output Logic Form:	
Transistor-transistor lo	ygic
Input Circuit Pattern	
10 input	
Case Outline Source	And Designator:
D-2 mil-m-38510	
Terminal Surface Tre	atment:
Solder	
Voltage Rating And ⁻	Type Per Characteristic:
7.0 volts power sourc	e
Time Rating Per Cha	cteristic:
35.00 nanoseconds p	propagation delay time, low to high level output and 35.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type	
Rom	
Test Data Document	:
96906-mil-std-883 sta	ndard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And G	Quantity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	

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